

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S3	212	(GaN or (gallium near nitride)) and (single near crystal) and (half near width) and diffraction	US-PGPUB; USPAT	OR	ON	2007/01/23 10:27
S44	252	(117/952).CCLS.	USPAT; USOCR	OR	OFF	2007/01/22 15:53
S45	82	S44 and ("halfwidth" or half near "3" width)	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/22 15:54
S46	32	S44 and ("halfwidth" or (half near3 width))	US-PGPUB; USPAT; USOCR	OR	ON	2007/01/22 15:55
S47	8	(diffraction near plane) with nitride	US-PGPUB; USPAT	OR	ON	2007/01/23 10:43
S48	12444	"428"/\$ and diffraction	US-PGPUB; USPAT	OR	ON	2007/01/23 10:43
S49	3423	"428"/\$ and diffraction and nitride	US-PGPUB; USPAT	OR	ON	2007/01/23 10:43
S50	1335	"428"/\$ and diffraction and nitride and semiconductor	US-PGPUB; USPAT	OR	ON	2007/01/23 11:07
S51	40	diffraction and nitride and semiconductor	EPO; JPO	OR	ON	2007/01/23 11:09
S52	328	diffraction and nitride	EPO; JPO	OR	ON	2007/01/23 11:09
S53	5343	(LED or "light emitting") with nitride	US-PGPUB; USPAT	OR	ON	2007/01/24 17:49
S54	1272	(LED or "light emitting") with nitride and AIN with substrate	US-PGPUB; USPAT	OR	ON	2007/01/24 17:51
S55	132	((LED or "light emitting") with nitride with epitaxial) and AIN with substrate	US-PGPUB; USPAT	OR	ON	2007/01/24 17:52